鑫沃科技
XIN WO TECHNOLOGY

产品规格手册

PRODUCT SPECIFICATION MANUAL

CJE3134K

N Channel Advanced Power MOSFET
SOT523/20V/1.2A

深圳东为电子科技有限公司
DONGWEI ELECTRONIC TECHNOLOGY CO.,LTD

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
20V	110mΩ@4.5V	1.2A
	150mΩ@2.5V	

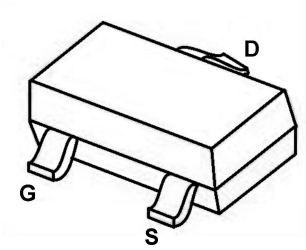
Feature

- Surface Mount Package
- N-Channel Switch with Low R_{DS}(on)
- Operated at Low Logic Level Gate Drive
- ESD Protected

Application

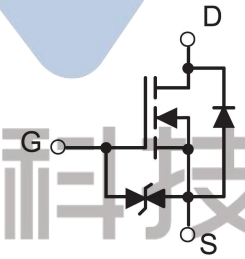
- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

Package

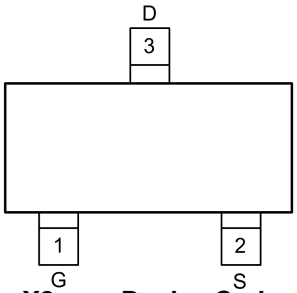


SOT-523

Circuit diagram



Marking



X2 =Device Code

Absolute maximum ratings (Ta=25℃ unless otherwise noted)

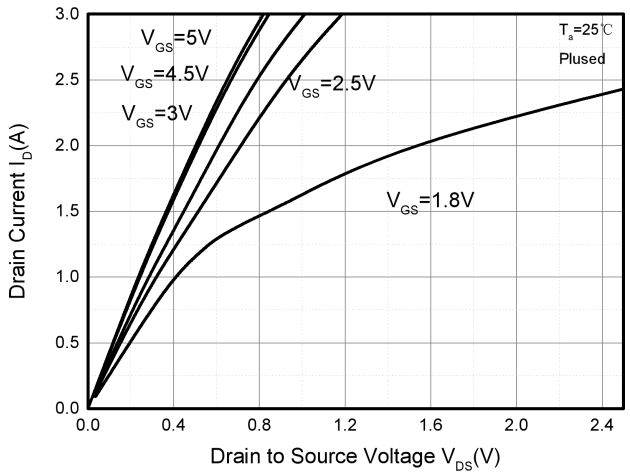
Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±12	V
Continuous Drain Current	I_D	1.2	A
Pulsed Drain Current	I_{DM}	1.8	A
Power Dissipation	P_D	0.15	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	833	℃/W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{STG}	-55~ +150	℃

Electrical characteristics (T_A=25 °C, unless otherwise noted)

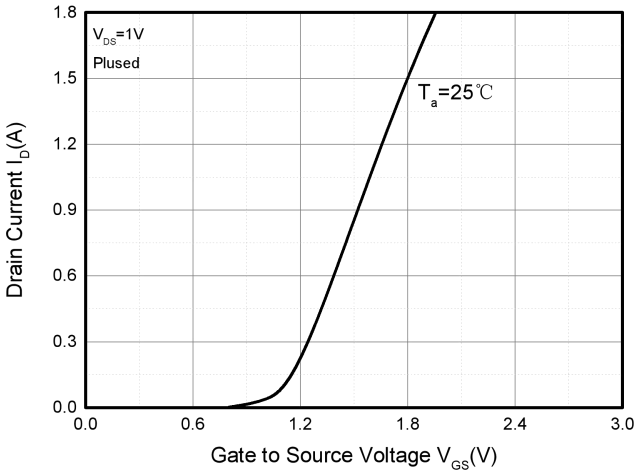
Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	20			V
Zero gate voltage drain current	I_{DSS}	V_{DS} =16V,V_{GS} = 0V			1	μA
Gate-body leakage current	I_{GSS}	V_{GS} =±10V, V_{DS} = 0V			±10	uA
Gate threshold voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	0.3	0.65	1	V
Drain-source on-resistance	$R_{DS(on)}$	V_{GS} = 4.5V, I_D = 1.2A		90	110	mΩ
		V_{GS} =2.5V, I_D = 0.8A		115	150	
		V_{GS} =1.8V, I_D = 0.3A		165	215	
Dynamic characteristics						
Input Capacitance	C_{iss}	V_{DS} =16V,V_{GS} =0V, f=1MHz		79	120	pF
Output Capacitance	C_{oss}			13	20	
Reverse Transfer Capacitance	C_{rss}			9	15	
Switching Characteristics						
Turn-on delay time	$t_{d(on)}$	V_{GS}=4.5V,V_{DS}=10V, I_D =500mA,R_{GEN}=10Ω		6.7		ns
Turn-on rise time	t_r			4.8		
Turn-off delay time	$t_{d(off)}$			17.3		
Turn-off fall time	t_f			7.4		
Source-Drain Diode characteristics						
Body Diode Voltage	V_{SD}	I_S=0.5A, V_{GS} = 0V		0.7	1.3	V

Typical Characteristics

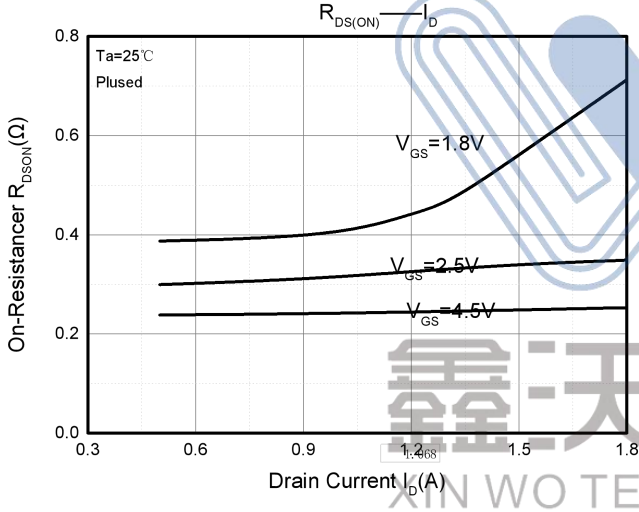
Output Characteristics



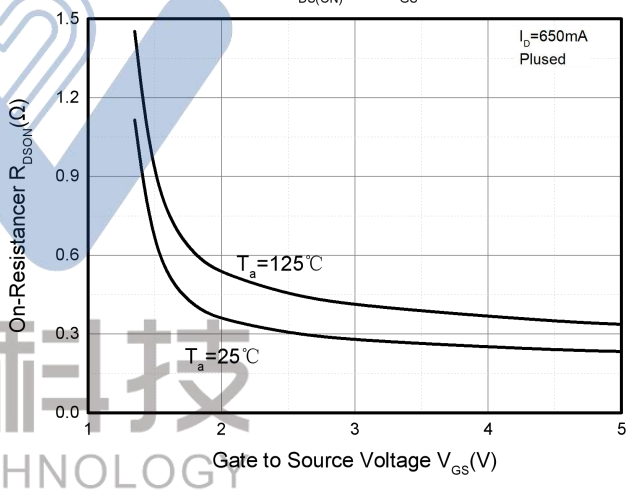
Transfer Characteristics



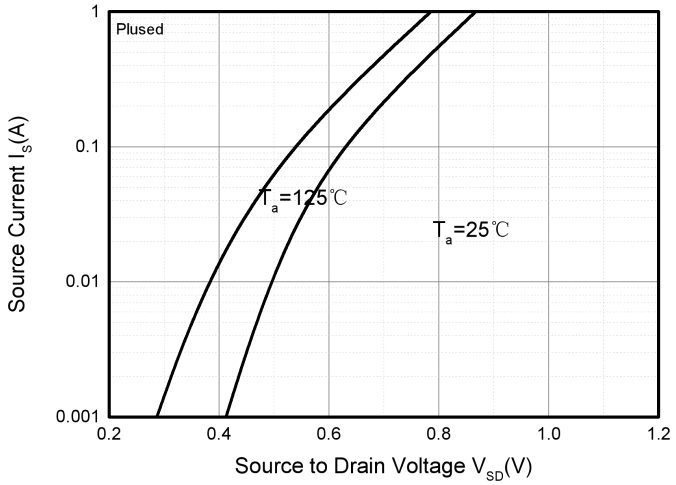
$R_{DS(ON)}$——I_D



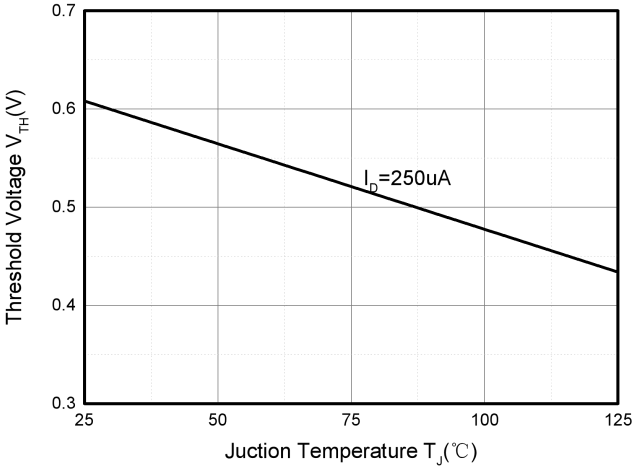
$R_{DS(ON)}$——V_{GS}



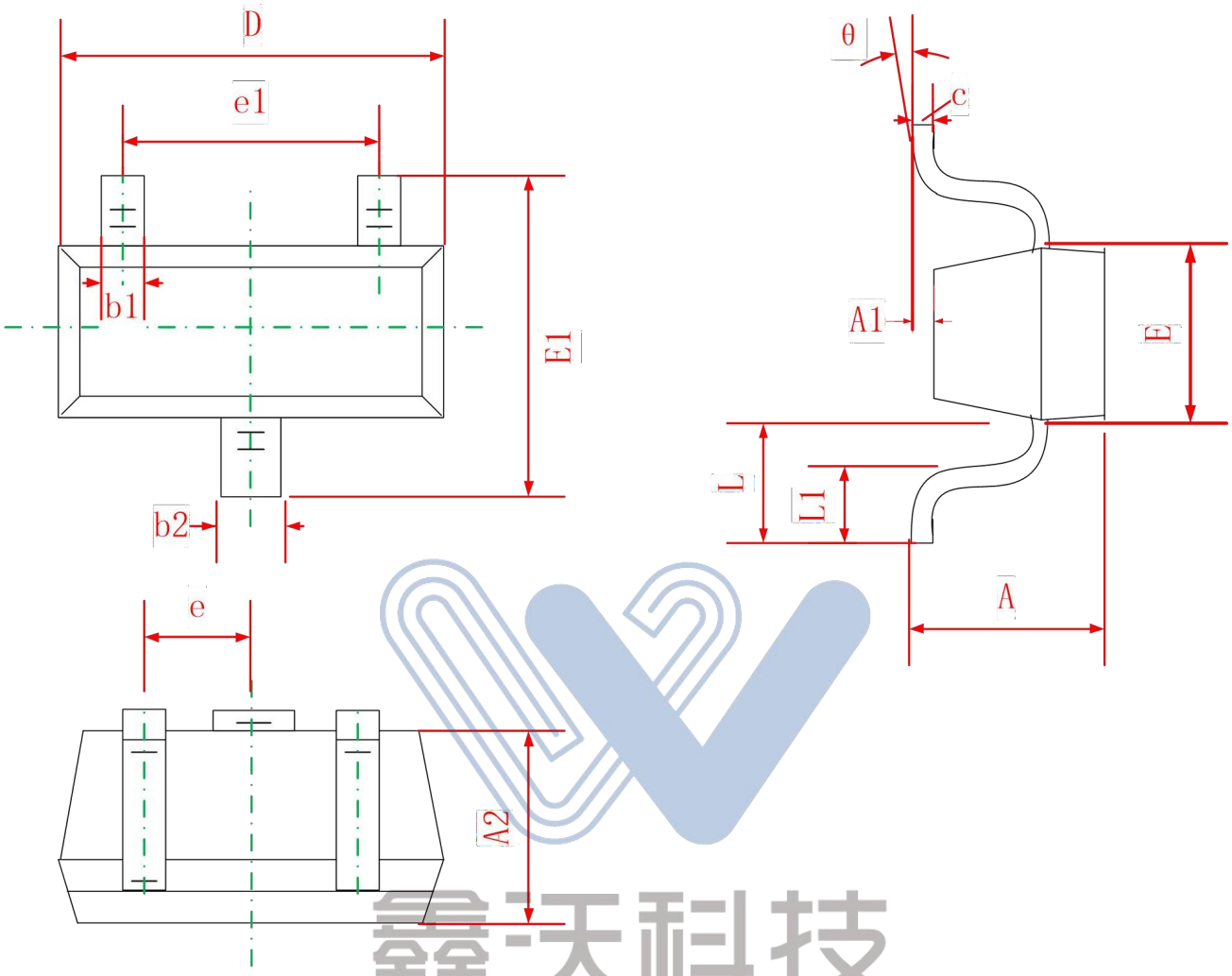
I_S——V_{SD}



Threshold Voltage



SOT-523 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
C	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500 TYP	
e1	0.900	1.100
L	0.400 REF	
L1	0.260	0.460
θ	0°	8°